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,	INFORMATIO	N DISCLOSURE	•	Filing Date	Herewith 1//21/03			
. *	STATEMENT	BY APPLICANT		First Named Inventor	Yuanning Chen, et al.			
			r	Group Art Unit	2813			
Sheet	(use as many s	heets as necessary)		Examiner Name	Jack S J Chen			
Sheet		of of		Attorney Docket No.	TI-35022.2			

	1			U.S. I	PATENT DOCUM	ENTS		
Exam. Initials*		U.S. Patent Document		Name of Patentee	Date of Pub.			
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